

SFF150/61

14849 Firestone Boulevard · La Mirada, CA 90638
 Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

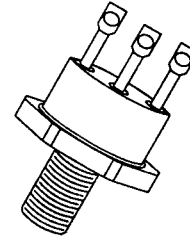
Designer's Data Sheet

FEATURES:

- Rugged construction with poly silicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Hermetically sealed power package
- TX, TXV and Space Level screening available
- Screening in accordance with MIL-S-19500/543C is available
- Replaces: IRF150 Types

**30 AMP
 100 VOLTS
 0.055 Ω
 N-CHANNEL
 POWER MOSFET**

TO-61



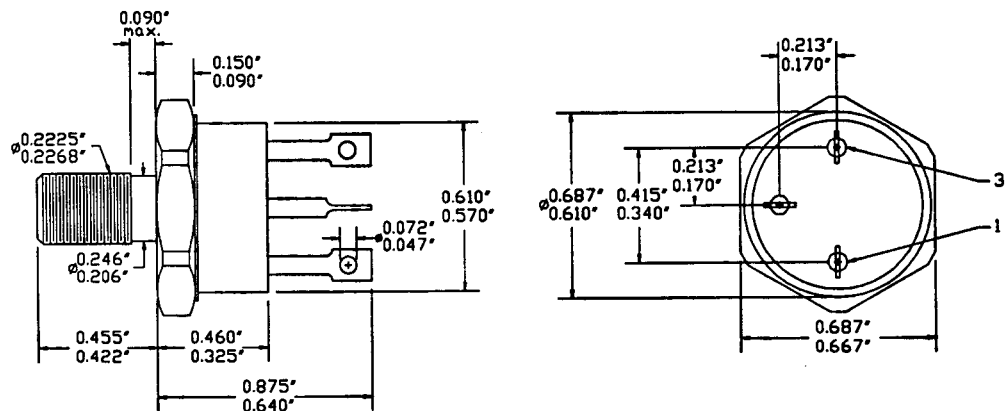
MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	100	Volts
Gate to Source Voltage	V _{GS}	± 20	Volts
Continuous Drain Current	I _D	30	Amps
Operating and Storage Temperature	T _{op} & T _{stg}	-55 to +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	1	°C/W
Total Device Dissipation @ TC=25°C	P _D	125	Watts
Total Device Dissipation @ TC=55°C		95	

PACKAGE OUTLINE: TO-61

PIN OUT:

**PIN 1: SOURCE
 PIN 2: GATE
 PIN 3: DRAIN**



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F00039 B

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SFF150/61

PRELIMINARY

**SOLID STATE DEVICES, INC**14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424**ELECTRICAL CHARACTERISTICS @ T_J=25°C (Unless Otherwise Specified)**

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (VGS=0 V, ID=250μA)		BV _{DSS}	100	---	---	V
Drain to Source on State Resistance (VGS=10 V, ID=20 A)		R _{DS(on)}	---	---	0.055	Ω
On State Drain Current (VDS > ID(on) X RDS(on) Max, VGS=10 V)		ID(on)	30	---	---	A
Gate Threshold Voltage (VDS=VGS, ID=250μA)		VGS(th)	2	---	4	V
Forward Transconductance (VDS > ID(on) X RDS(on) Max, IDS=20 A)		g _{fs}	9	11	---	S(τ)
Zero Gate Voltage Drain Current (VDS=max rated voltage, VGS=0 V) (VDS=80% rated VDS, VGS=0 V, TA=125°C)		IDSS	---	---	250 1000	μA
Gate to Source Leakage Forward Gate to Source Leakage Reverse	At rated VGS	IGSS	---	---	100 100	nA
Total Gate Charge Gate to Source Charge Gate to Drain Charge	VGS=10 Volts 80% rated VDS Rated ID	Q _g Q _{gs} Q _{gd}	---	63 27 36	120 ---	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	VDD= 24 V ID= 20 A RG= 6.2 Ω	td(on) tr td(off) tf	---	---	35 100 125 100	nsec
Diode Forward Voltage (IS= 40 A, VGS=0 V, T _J =25°C)		VSD	---	---	2.5	V
Diode Reverse Recovery Time Reverse Recovery Charge	T _J =25°C IF=40 A di/dt=100 A/μsec	t _{rr} Q _{RR}	---	600 3.3	---	nsec μC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	VGS=0 Volts VDS=25 Volts f= 1 MHz	C _{iss} C _{oss} C _{rss}	---	2000 1000 350	3000 1500 500	pF

For thermal derating curves and other characteristic curves please contact SSDI Marketing Department.